



#### 50V PNP POWER SWITCHING TRANSISTOR IN SOT89

#### **Description**

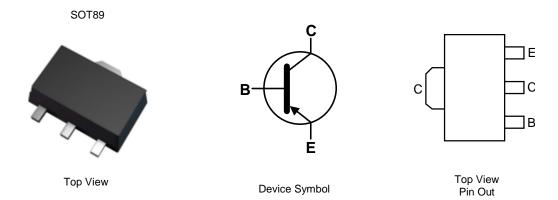
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

#### **Features**

- BV<sub>CEO</sub> > -50V
- I<sub>C</sub> = -2A High Continuous Collector Current
- High Gain Holds up
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.052 grams (Approximate)



#### Ordering Information (Notes 4 and 5)

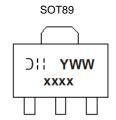
Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel	
2DA1213YQ-13	P25Y	13	12	2,500	

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

### **Marking Information**

Notes:



OH = Manufacturer's Marking

xxxx = P25Y = Product Type Marking Code

YWW = Date Code Marking

Y = Last Digit of Year (ex: 8 = 2018)

WW = Week Code (01 to 53)



### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-50	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Continuous Collector Current	Ic	-2	Α
Peak Pulse Current	Ісм	-2.5	Α
Base Current	I <sub>B</sub>	-500	mA

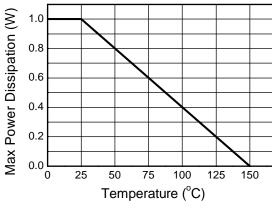
### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

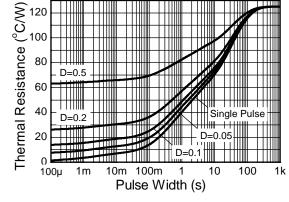
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	125	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R <sub>0JL</sub>	18.3	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes:

- 6. For a device surface mounted on 15mm x 15mm x 0.6mm FR-4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in steady state condition.
- 7. Thermal resistance from junction to solder-point (on the exposed collector pad).

# Thermal Characteristics and Derating Information





#### **Derating Curve**

**Pulse Power Dissipation** 

**Transient Thermal Impedance** 

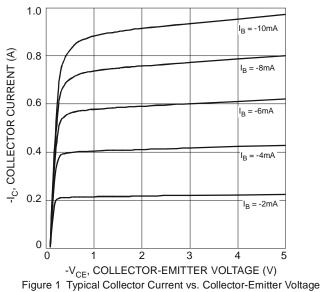


# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	_	_	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	-50	_	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	_	_	V	$I_E = -100 \mu A$
Collector Cut-off Current	I <sub>CBO</sub>	_	_	-100	nA	V <sub>CB</sub> = -50V
Emitter Cut-off Current	I <sub>EBO</sub>	_	_	-100	nA	$V_{EB} = -5V$
DC Current Gain (Note 8)	h <sub>FE</sub>	120		240	_	$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 8)		20		_		$I_C = -2A$ , $V_{CE} = -2V$
Collector-Emitter Saturation Voltage (Note 8)	V <sub>CE(sat)</sub>	_	-	-0.5	V	$I_C = -1A$ , $I_B = -50mA$
Base-Emitter Saturation Voltage (Note 8)	V <sub>BE(sat)</sub>	_		-1.2	V	$I_C = -1A$ , $I_B = -50mA$
Transition Frequency	f <sub>T</sub>		160	-	MHz	$I_C = -100 \text{mA}, V_{CE} = -2 \text{V},$ f = 100 MHz
Output Capacitance	C <sub>obo</sub>	_	17	_	pF	$V_{CB} = -10V$ , $I_E = 0$ , $f = 1MHz$
Turn-On Time	ton	_	25	_	ns	)/ O)/ I 4A
Storage Time	t <sub>(s)</sub>	_	130	_	ns	$V_{CE}$ = -2V, $I_{C}$ = -1A, $I_{B1}$ = - $I_{B2}$ = -50mA
Fall Time	t <sub>(f)</sub>	_	12		ns	1B1 = -1B2 = -30111A

Note:

# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



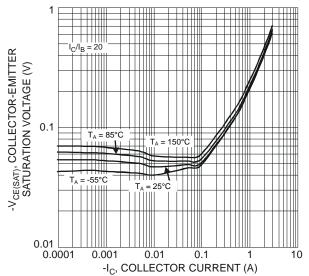


Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

<sup>8.</sup> Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



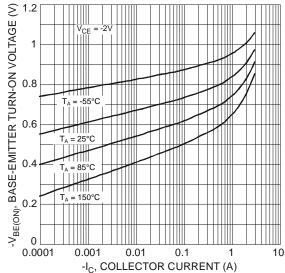


Figure 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

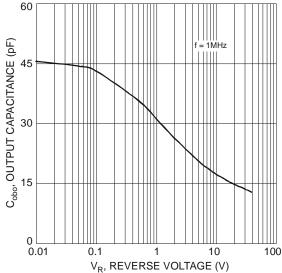


Figure 5 Typical Output Capacitance Characteristics

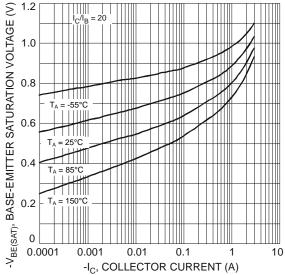


Figure 4 Typical Base-Emitter Saturation Voltage vs. Collector Current

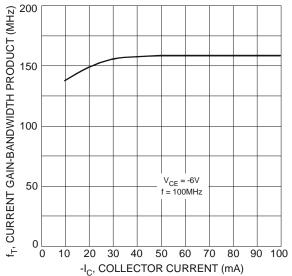


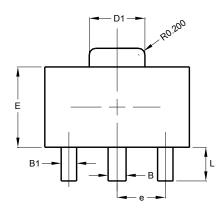
Figure 6 Typical Gain-Bandwidth Product vs. Collector Current

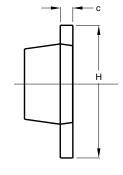


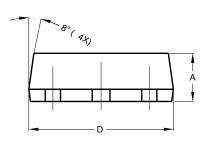
## **Package Outline Dimensions**

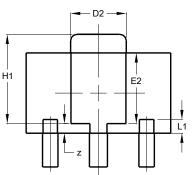
Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT89







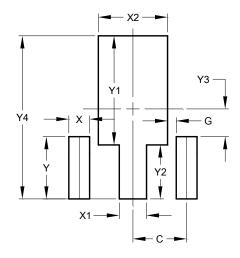


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT89



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Y	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		



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